

N- and P-Channel 30 V (D-S) MOSFET

| PRODUCT SUMMARY | | | | |
|-----------------|---------------------|------------------------------------|---------------------------------|-----------------------|
| | V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) ^a | Q _g (Typ.) |
| N-Channel | 30 | 0.014 at V _{GS} = 10 V | 26 | 20.2 |
| | | 0.018 at V _{GS} = 4.5 V | 22 | |
| P-Channel | - 30 | 0.027 at V _{GS} = - 10 V | - 21 | 15.1 |
| | | 0.035 at V _{GS} = - 4.5 V | - 19 | |

FEATURES

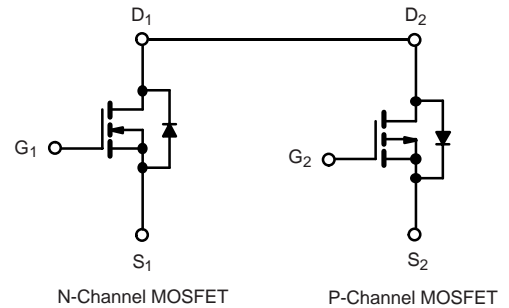
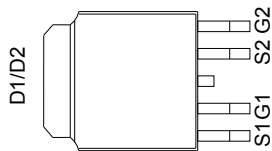
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Inverter

TO-252-4L



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

| Parameter | Symbol | N-Channel | P-Channel | Unit | |
|--|-----------------------------------|------------------------|----------------------|----------------------|-----------------------|
| Drain-Source Voltage | V _{DS} | 30 | - 30 | V | |
| Gate-Source Voltage | V _{GS} | ± 20 | ± 20 | | |
| Continuous Drain Current (T _J = 150 °C) | I _D | T _C = 25 °C | 26 | A | |
| | | T _C = 70 °C | 22 | | |
| | | T _A = 25 °C | 8.0 ^{b, c} | | - 7.2 ^{b, c} |
| | | T _A = 70 °C | 6.2 ^{b, c} | | - 5.8 ^{b, c} |
| Pulsed Drain Current (10 μs Pulse Width) | I _{DM} | 78 | -63 | A | |
| Source-Drain Current Diode Current | I _S | T _C = 25 °C | 26 | | |
| | | T _A = 25 °C | 21 ^{b, c} | - 19 ^{b, c} | |
| Pulsed Source-Drain Current | I _{SM} | 78 | - 60 | mJ | |
| Single Pulse Avalanche Current | I _{AS} | 10 | - 20 | | |
| Single Pulse Avalanche Energy | E _{AS} | 5 | 20 | W | |
| Maximum Power Dissipation | P _D | T _C = 25 °C | 31 | | |
| | | T _C = 70 °C | 13 | | 9 |
| | | T _A = 25 °C | 9 ^{b, c} | | 8 ^{b, c} |
| | | T _A = 70 °C | 7.28 ^{b, c} | 6.59 ^{b, c} | |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | - 55 to 150 | | °C | |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | N-Channel | | P-Channel | | Unit |
|---|-------------------|-----------|------|-----------|------|------|
| | | Typ. | Max. | Typ. | Max. | |
| Maximum Junction-to-Ambient ^{b, d} | R _{thJA} | 50 | 62.5 | 47 | 62.5 | °C/W |
| Maximum Junction-to-Foot (Drain) | R _{thJF} | 30 | 40 | 29 | 38 | |

Notes:

- Based on T_C = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 120 °C/W (N-Channel) and 110 °C/W (P-Channel).

| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | | | |
|--|-------------------------|--|------|-------------------|-------|-----------|----------------------|----------|
| Parameter | Symbol | Test Conditions | Min. | Typ. ^a | Max. | Unit | | |
| Static | | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | N-Ch | 30 | | | V | |
| | | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$ | P-Ch | -30 | | | | |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | N-Ch | | 40 | | mV/ $^\circ\text{C}$ | |
| | | $I_D = -250\text{ }\mu\text{A}$ | P-Ch | | -40 | | | |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | N-Ch | | -4.1 | | | |
| | | $I_D = -250\text{ }\mu\text{A}$ | P-Ch | | 5.0 | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | N-Ch | 1.0 | | 3.0 | V | |
| | | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$ | P-Ch | -1.0 | | -3.0 | | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | N-Ch | | | ± 100 | nA | |
| | | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | P-Ch | | | ± 100 | | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$ | N-Ch | | | 1 | μA | |
| | | $V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$ | P-Ch | | | -1 | | |
| | | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | N-Ch | | | 10 | | |
| | | $V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | P-Ch | | | -10 | | |
| On-State Drain Current ^b | $I_{D(on)}$ | $V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$ | N-Ch | 26 | | | A | |
| | | $V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$ | P-Ch | -21 | | | | |
| Drain-Source On-State Resistance ^b | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 8\text{ A}$ | N-Ch | | 0.014 | 0.0185 | Ω | |
| | | $V_{GS} = -10\text{ V}, I_D = -8\text{ A}$ | P-Ch | | 0.027 | 0.040 | | |
| | | $V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$ | N-Ch | | 0.018 | 0.022 | | |
| | | $V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$ | P-Ch | | 0.035 | 0.046 | | |
| Forward Transconductance ^b | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 8\text{ A}$ | N-Ch | | 27 | | S | |
| | | $V_{DS} = -15\text{ V}, I_D = -8\text{ A}$ | P-Ch | | 25 | | | |
| Dynamic^a | | | | | | | | |
| Input Capacitance | C_{iss} | N-Channel $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | N-Ch | | 546 | | pF | |
| Output Capacitance | C_{oss} | | P-Ch | | 750 | | | |
| Reverse Transfer Capacitance | C_{rss} | P-Channel $V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | N-Ch | | 110 | | | |
| | | | P-Ch | | 223 | | | |
| Total Gate Charge | Q_g | $V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$ | N-Ch | | 19.5 | 30 | nC | |
| | | $V_{DS} = -20\text{ V}, V_{GS} = -10\text{ V}, I_D = -10\text{ A}$ | P-Ch | | 36.5 | 53 | | |
| | | N-Channel $V_{DS} = 20\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$ | N-Ch | | 20.2 | 30 | | |
| | | | P-Ch | | 15.1 | 27 | | |
| Gate-Source Charge | Q_{gs} | P-Channel $V_{DS} = -20\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$ | N-Ch | | 2.5 | | | |
| Gate-Drain Charge | Q_{gd} | | P-Ch | | 5.1 | | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | N-Ch | 0.3 | 1.5 | 3.0 | | Ω |
| | | | P-Ch | 1.3 | 6.4 | 12.8 | | |

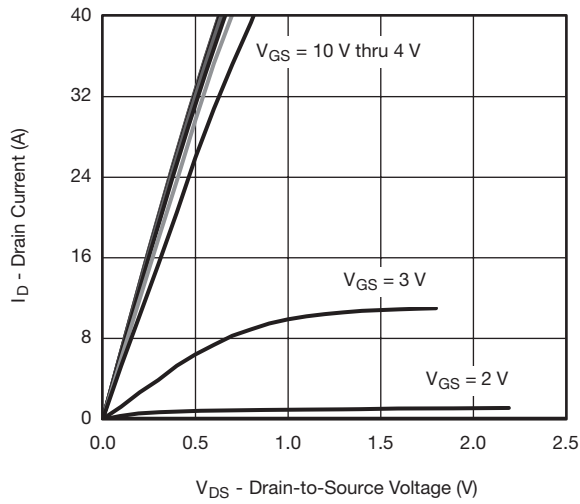
| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | | | |
|---|--------------|--|--|------|-------------------|-------|------|----|
| Parameter | Symbol | Test Conditions | | Min. | Typ. ^a | Max. | Unit | |
| Dynamic^a | | | | | | | | |
| Turn-On Delay Time | $t_{d(on)}$ | N-Channel $V_{DD} = 20\text{ V}, R_L = 2\ \Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\ \Omega$ | N-Ch | | 7 | 14 | ns | |
| Rise Time | t_r | | P-Ch | | 9 | 18 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | P-Channel $V_{DD} = -20\text{ V}, R_L = 2\ \Omega$ $I_D \cong -10\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\ \Omega$ | N-Ch | | 10 | 20 | | |
| | | | P-Ch | | 9 | 18 | | |
| Fall Time | t_f | | N-Ch | | 18 | 36 | | |
| | | | P-Ch | | 50 | 90 | | |
| Turn-On Delay Time | $t_{d(on)}$ | | N-Channel $V_{DD} = 20\text{ V}, R_L = 2\ \Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\ \Omega$ | N-Ch | | 9 | | 18 |
| | | | | P-Ch | | 14 | | 28 |
| Rise Time | t_r | | | N-Ch | | 11 | 22 | |
| | | | | P-Ch | | 42 | 75 | |
| Turn-Off Delay Time | $t_{d(off)}$ | N-Ch | | | 15 | 30 | | |
| | | P-Ch | | | 40 | 70 | | |
| Fall Time | t_f | N-Ch | | | 23 | 46 | | |
| | | P-Ch | | | 40 | 70 | | |
| Drain-Source Body Diode Characteristics | | | | | | | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25\text{ }^\circ\text{C}$ | N-Ch | | | 26 | A | |
| Pulse Diode Forward Current ^a | I_{SM} | | P-Ch | | | - 22 | | |
| Body Diode Voltage | V_{SD} | $I_S = 2\text{ A}$ $I_S = -2\text{ A}$ | N-Ch | | 0.74 | 1.2 | V | |
| | | | P-Ch | | - 0.77 | - 1.2 | | |
| Body Diode Reverse Recovery Time | t_{rr} | N-Channel $I_F = 5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ | N-Ch | | 17 | 34 | ns | |
| Body Diode Reverse Recovery Charge | Q_{rr} | | P-Ch | | 30 | 60 | | |
| Reverse Recovery Fall Time | t_a | P-Channel $I_F = -5\text{ A}, dI/dt = -100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ | N-Ch | | 10 | 20 | nC | |
| | | | P-Ch | | 26 | 52 | | |
| Reverse Recovery Rise Time | t_b | | N-Ch | | 10 | | ns | |
| | | | P-Ch | | 15 | | | |
| | | | N-Ch | | 7 | | | |
| | | | P-Ch | | 15 | | | |

Notes:

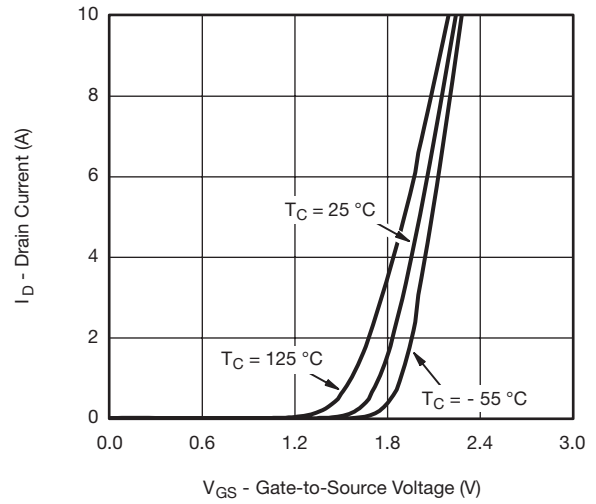
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

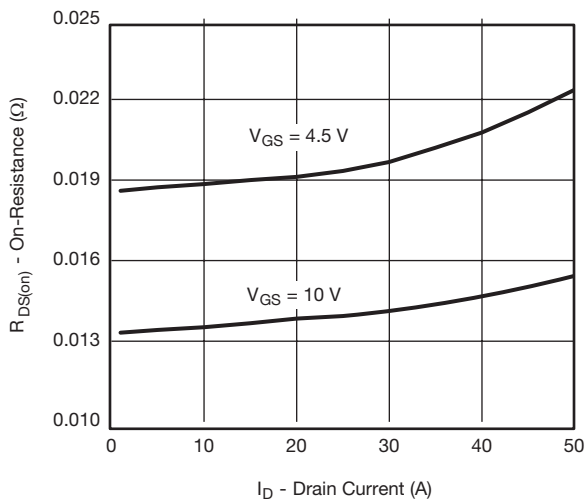
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



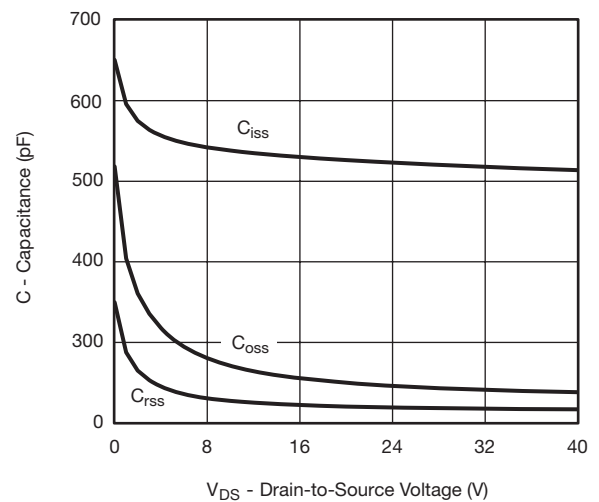
Output Characteristics



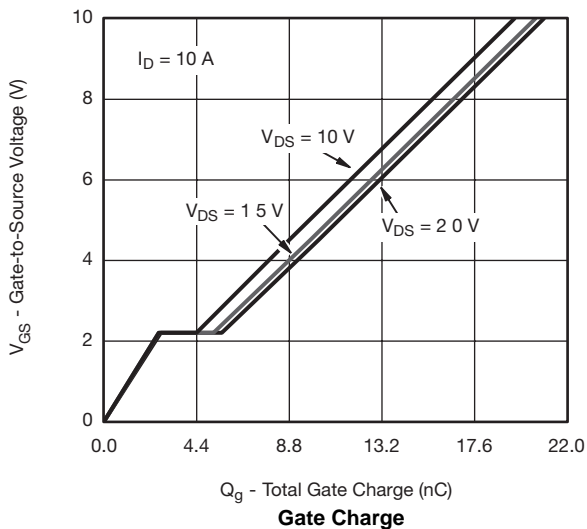
Transfer Characteristics



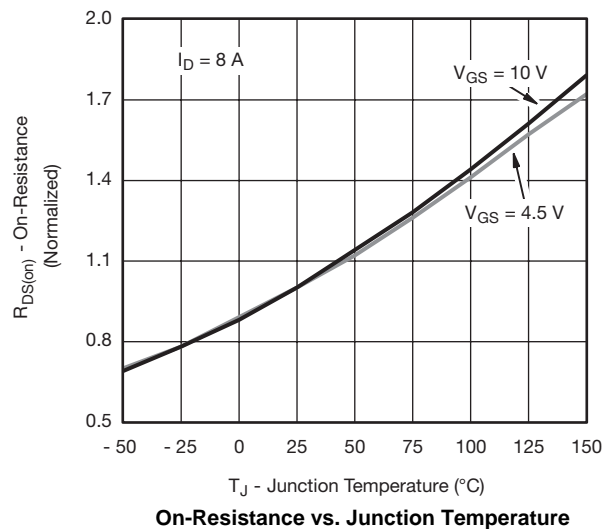
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

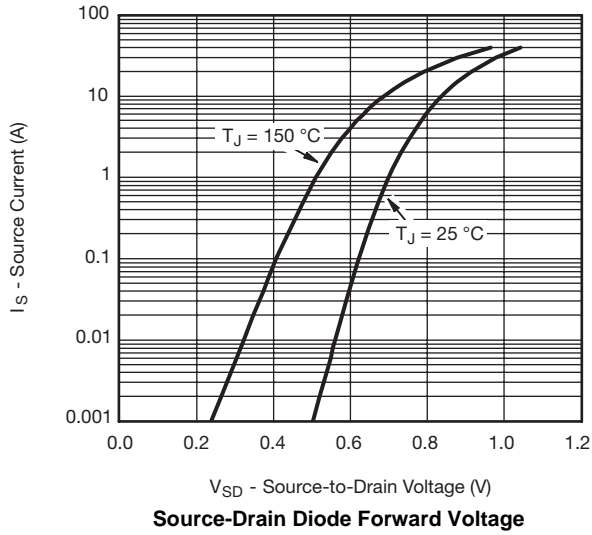


Gate Charge

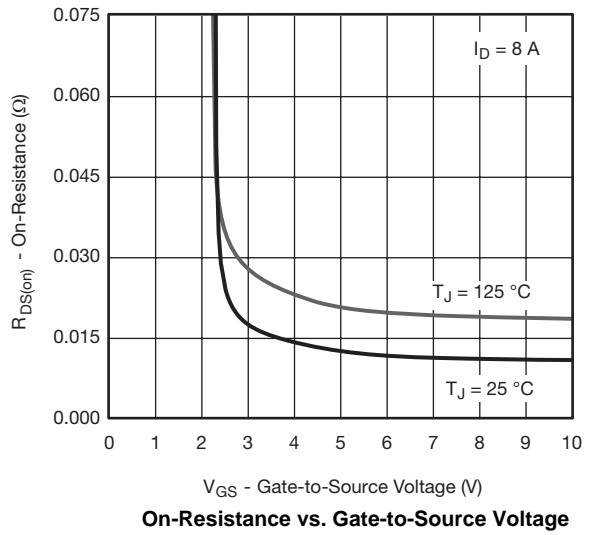


On-Resistance vs. Junction Temperature

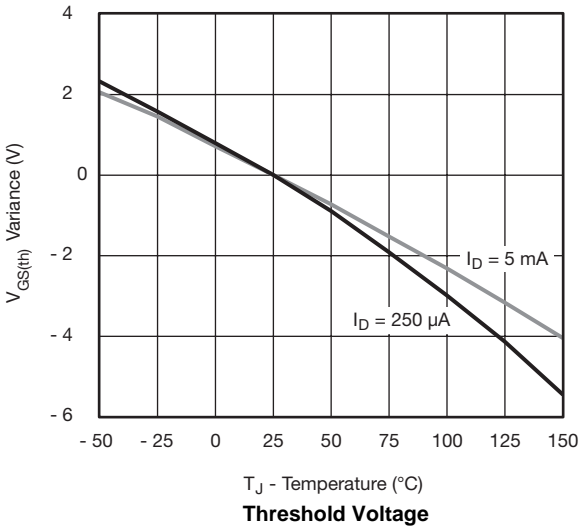
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



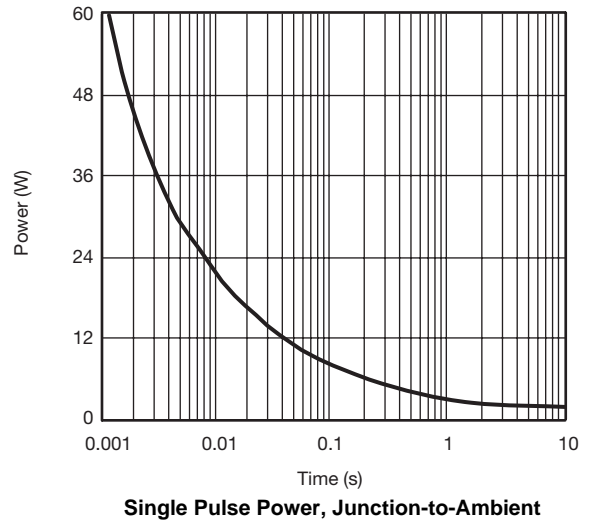
Source-Drain Diode Forward Voltage



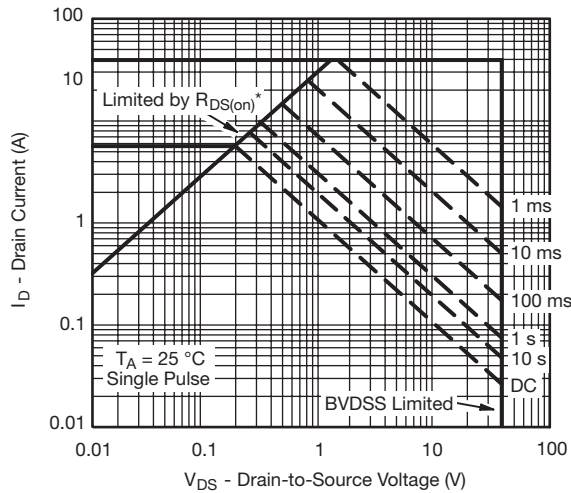
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



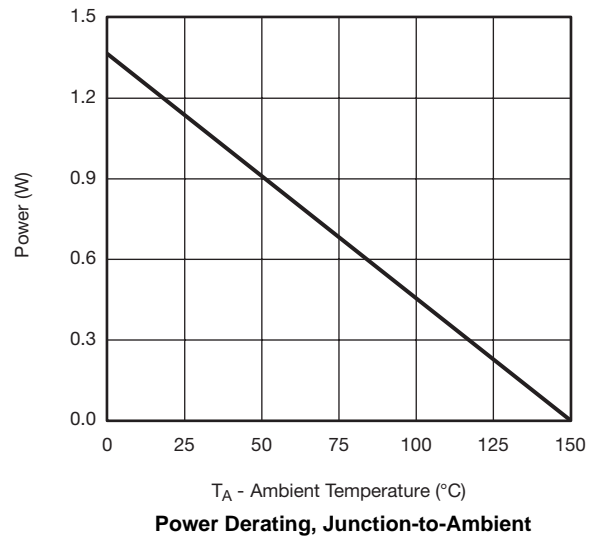
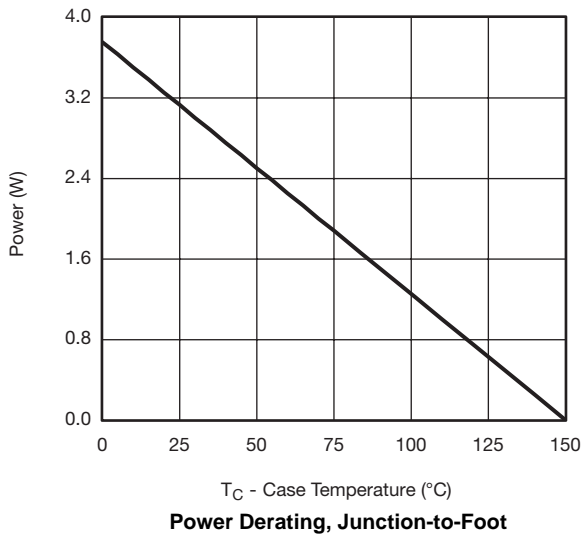
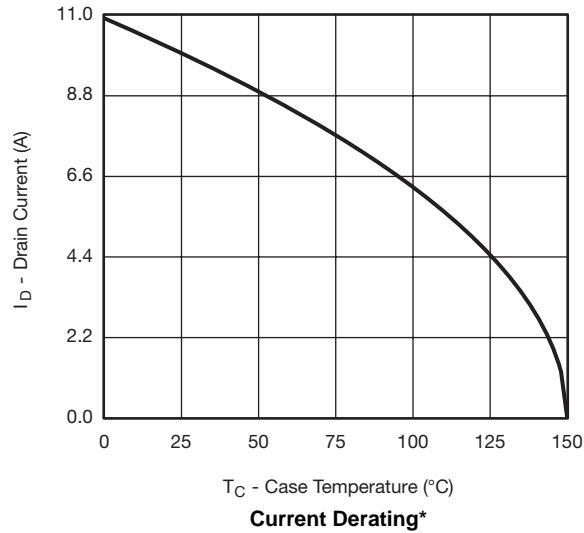
Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

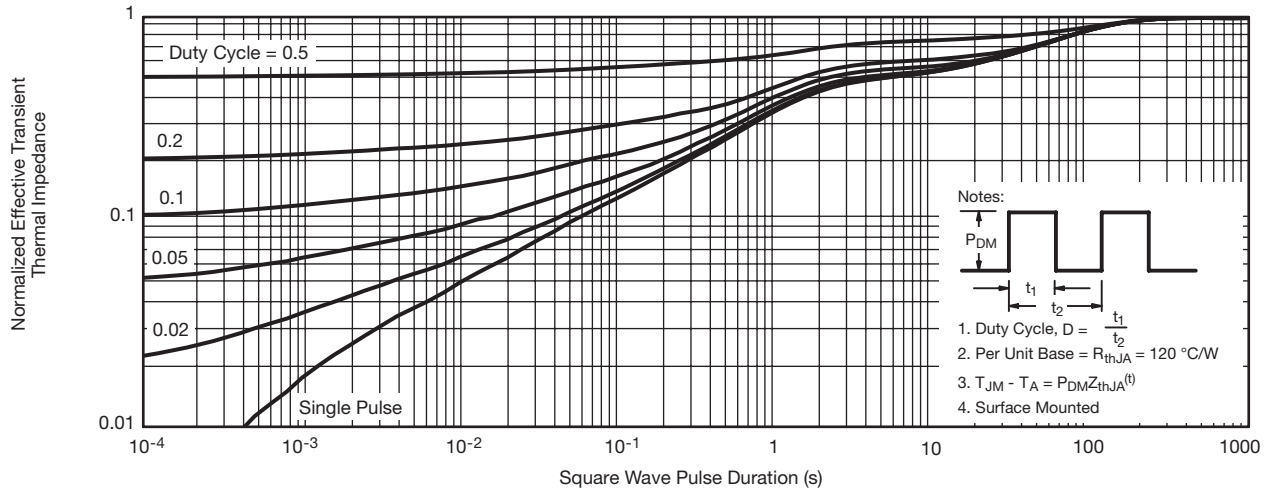
Safe Operating Area, Junction-to-Ambient

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

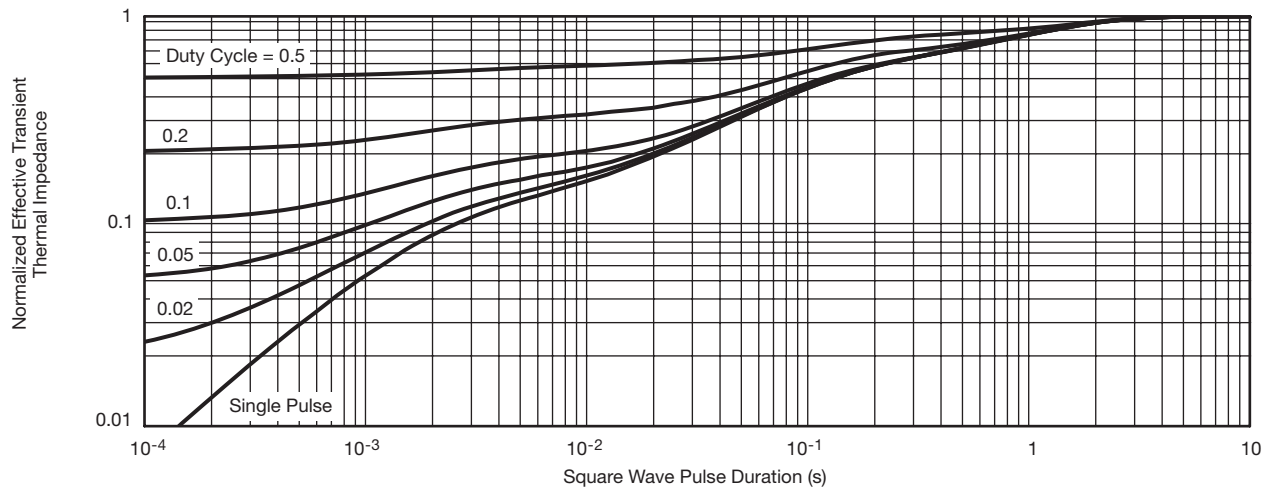


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

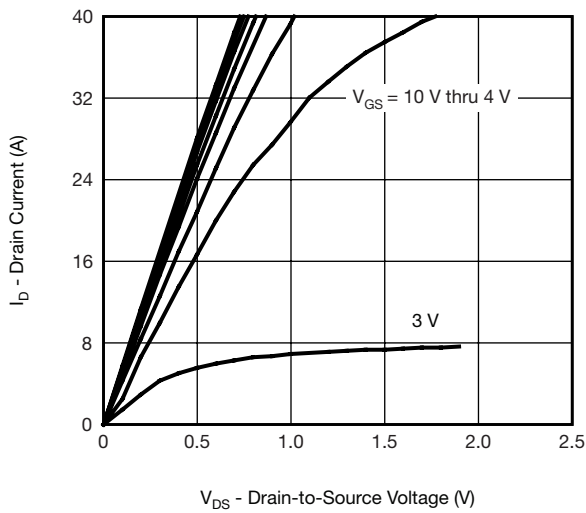


Normalized Thermal Transient Impedance, Junction-to-Ambient

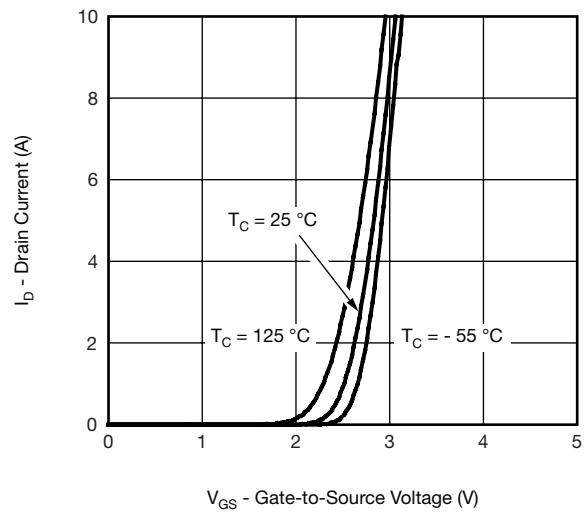


Normalized Thermal Transient Impedance, Junction-to-Foot

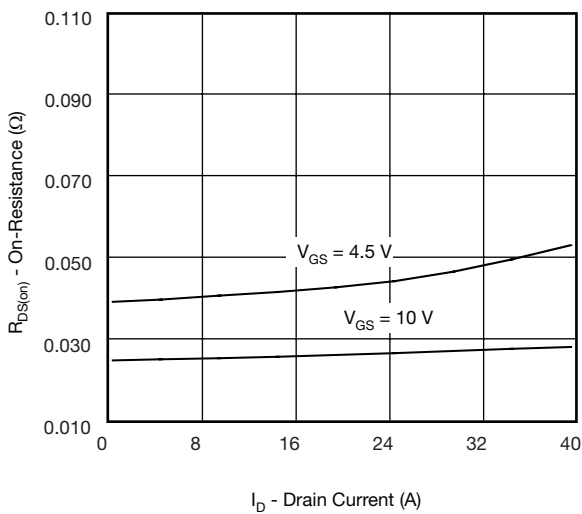
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



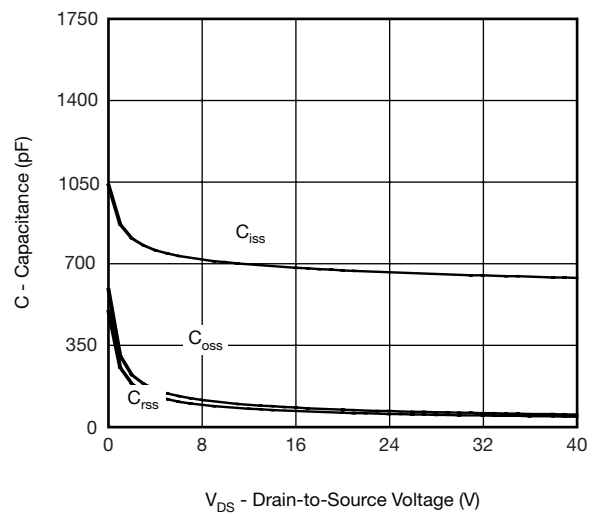
Output Characteristics



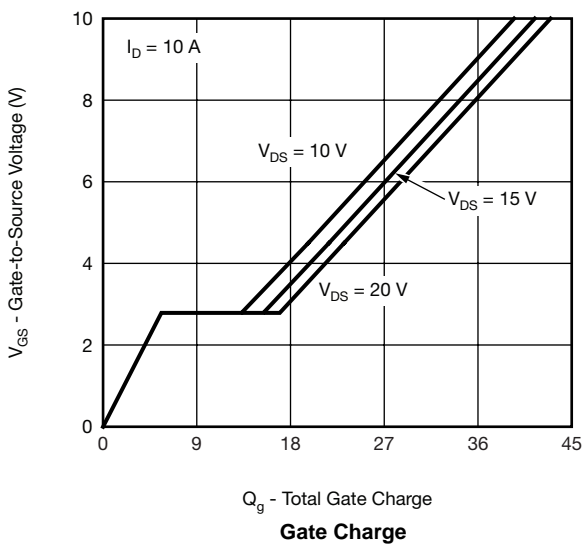
Transfer Characteristics



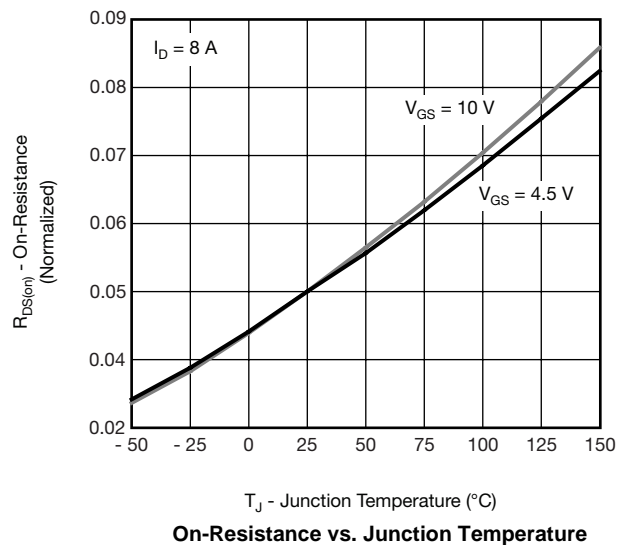
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

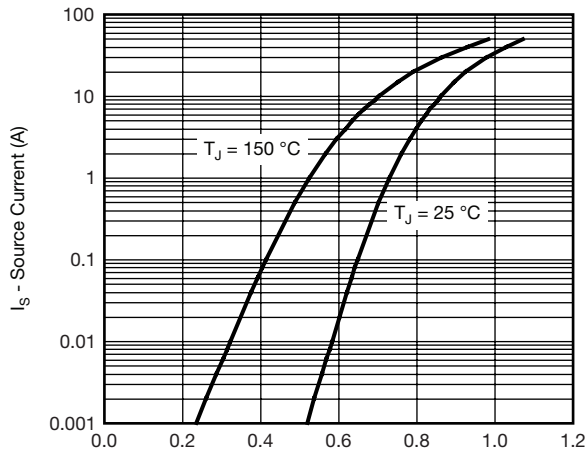


Gate Charge

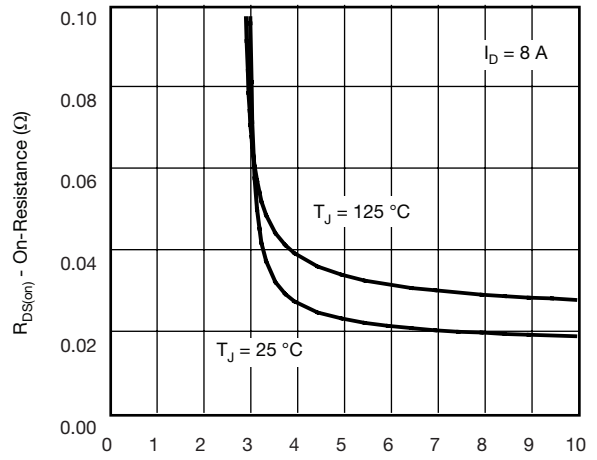


On-Resistance vs. Junction Temperature

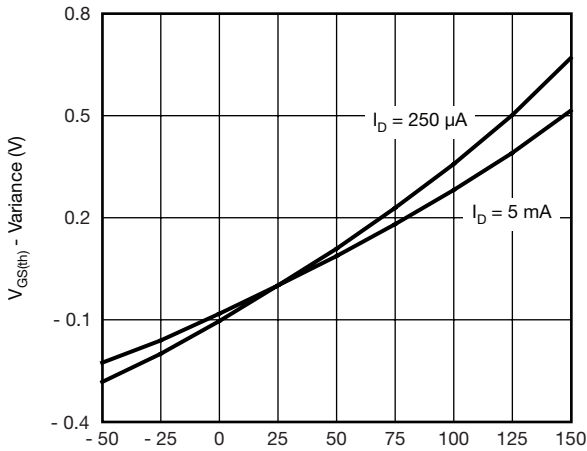
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



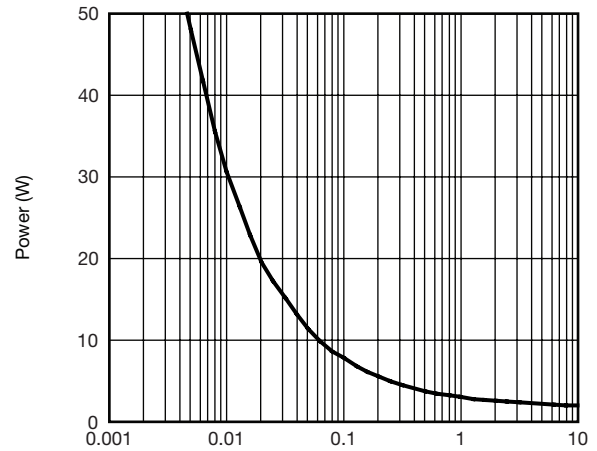
V_{SD} - Source-to-Drain Voltage (V)
Source-Drain Diode Forward Voltage



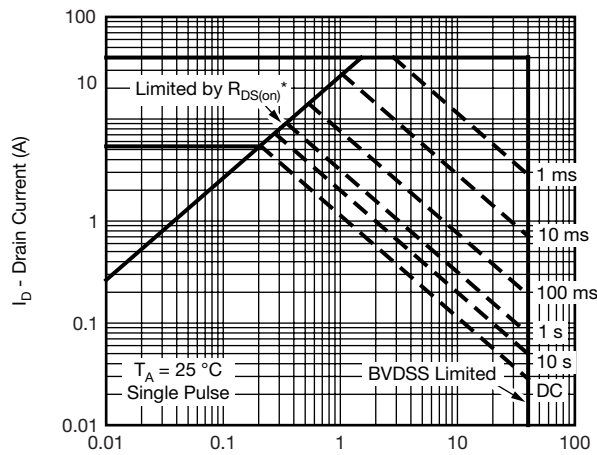
V_{GS} - Gate-to-Source Voltage (V)
On-Resistance vs. Gate-to-Source Voltage



T_J - Junction Temperature ($^\circ\text{C}$)
Threshold Voltage

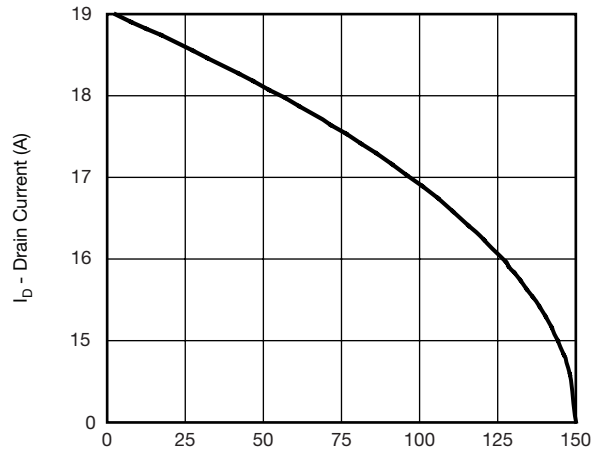


Single Pulse Power, Junction-to-Ambient



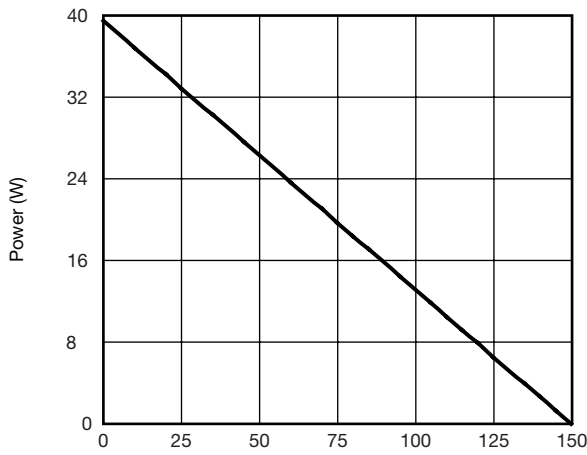
V_{DS} - Drain-to-Source Voltage (V)
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



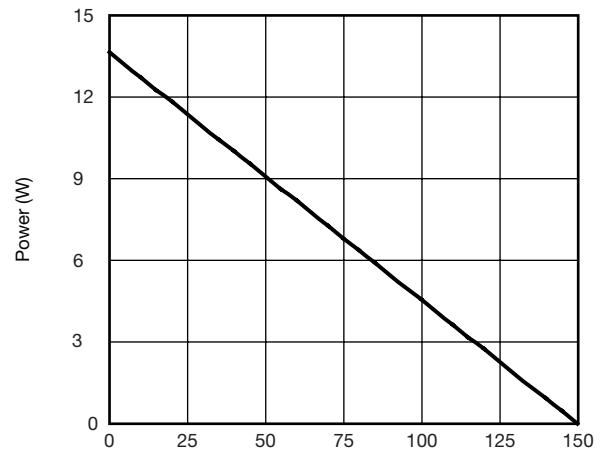
T_C - Case Temperature (°C)

Current Derating*



T_C - Case Temperature (°C)

Power Derating, Junction-to-Foot

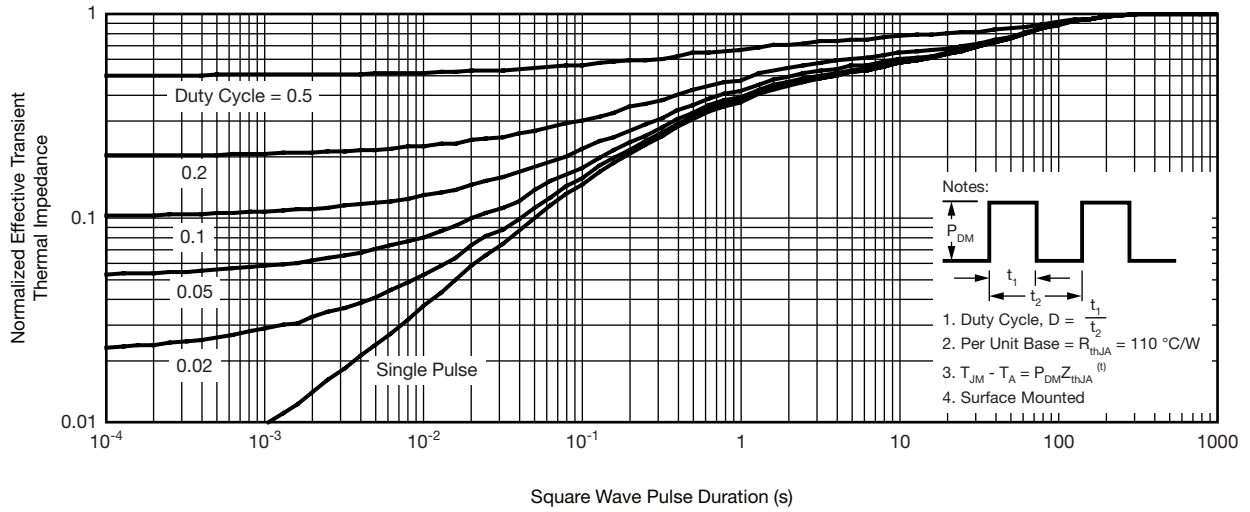


T_A - Ambient Temperature (°C)

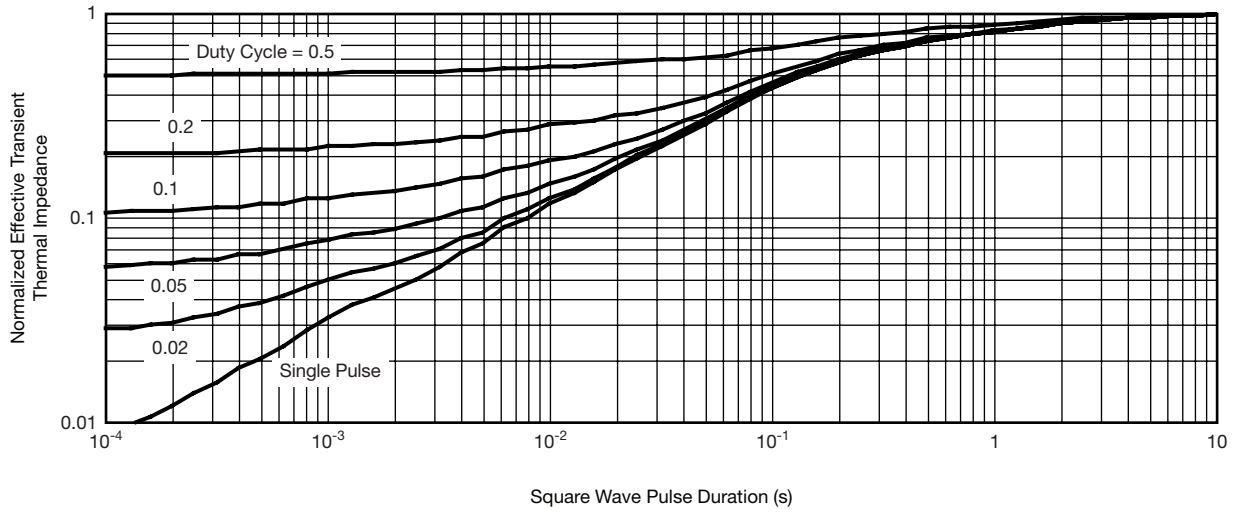
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



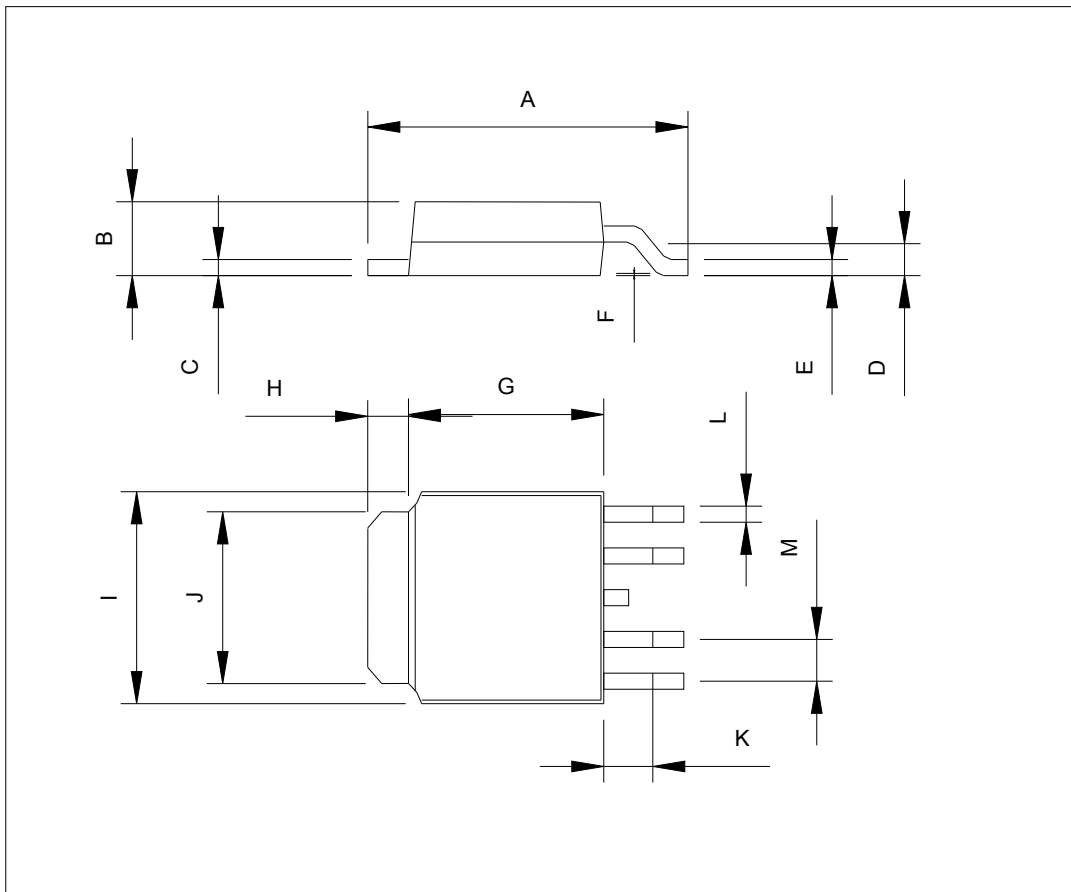
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

TO-252 (DPAK): 4-LEAD

| Dimension | mm | | | Dimension | mm | | |
|-----------|------|------|------|-----------|------|------|------|
| | Min. | Typ. | Max. | | Min. | Typ. | Max. |
| A | 9.0 | 9.5 | 10.0 | H | 1.3 | 1.5 | 1.7 |
| B | 2.1 | 2.3 | 2.5 | I | 6.3 | 6.5 | 6.7 |
| C | 0.4 | 0.5 | 0.6 | J | 4.8 | 5.0 | 5.2 |
| D | 1.1 | 1.2 | 1.3 | K | 0.8 | 1.3 | 1.8 |
| E | 0.4 | 0.5 | 0.6 | L | 0.3 | 0.5 | 0.7 |
| F | 0.00 | | 0.3 | M | 1.1 | 1.3 | 1.5 |
| G | 5.3 | 5.5 | 5.7 | N | | | |



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